

17P10

Power MOSFET

-17A, -100V P-CHANNEL POWER MOSFET

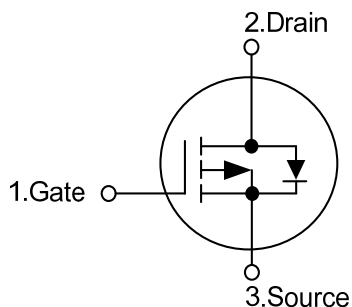
DESCRIPTION

The **17P10** uses advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable to be used in low voltage applications such as audio amplifier, high efficiency switching DC/DC converters, and DC motor control.

FEATURES

- * $R_{DS(ON)} \leq 0.18 \Omega$ @ $V_{GS} = -10V$, $I_D = -8.5A$
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified

SYMBOL

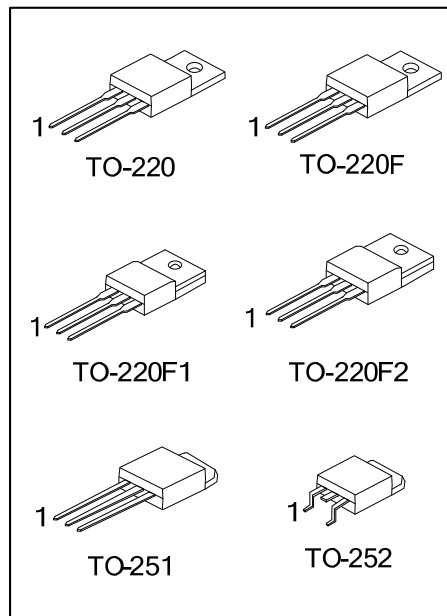


ORDERING INFORMATION

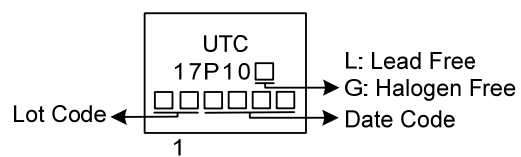
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
17P10L-TA3-T	17P10G-TA3-T	TO-220	G	D	S	Tube
17P10L-TF1-T	17P10G-TF1-T	TO-220F1	G	D	S	Tube
17P10L-TF2-T	17P10G-TF2-T	TO-220F2	G	D	S	Tube
17P10L-TF3-T	17P10G-TF3-T	TO-220F	G	D	S	Tube
17P10L-TM3-T	17P10G-TM3-T	TO-251	G	D	S	Tube
17P10L-TN3-R	17P10G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

17P10G-TA3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	-100	V
Gate-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current		I_D	-17	A
Pulsed Drain Current (Note 2)		I_{DM}	-52	A
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	62	mJ
Peak Diode Recovery dv/dt		dv/dt	2	V/ns
Power Dissipation	TO-220	P_D	120	W
	TO-220F/TO-220F1		42	W
	TO-220F2		52	W
	TO-251/TO-252		52	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=0.1\text{mH}$, $I_{AS}=-35.4\text{A}$, $V_{DD}=-50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$

4. $I_{SD}\leq -17\text{A}$, $di/dt \leq 200\mu\text{A/s}$, $V_{DD}\leq BV_{DS}$, Starting $T_J=25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^{\circ}\text{C/W}$
	TO-220F1/TO-220F2			
	TO-251/TO-252		110	
Junction to Case	TO-220	θ_{JC}	1.04	$^{\circ}\text{C/W}$
	TO-220F/TO-220F1		2.97	
	TO-220F2			
	TO-251/TO-252		2.4 (Note)	

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

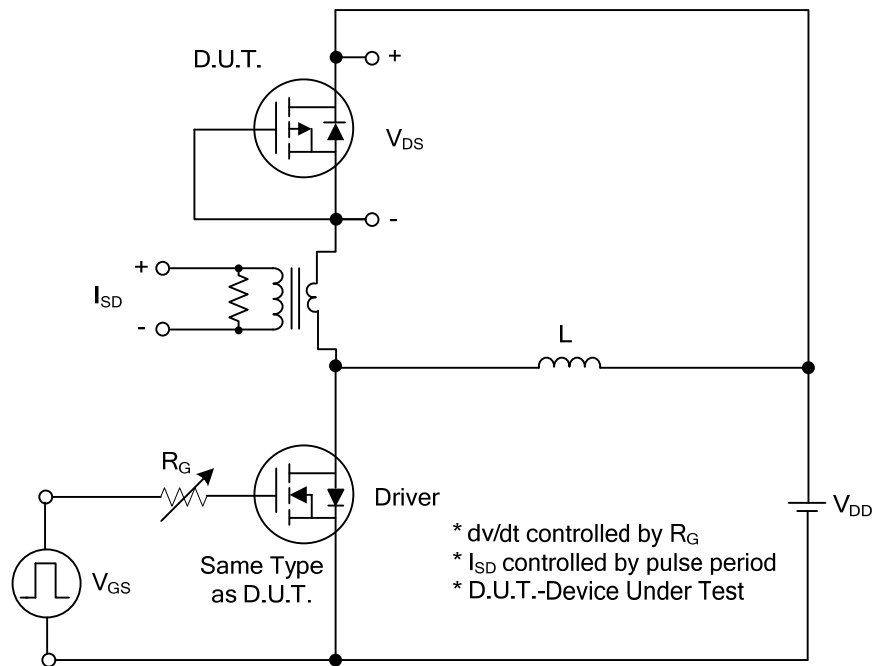
■ **ELECTRICAL CHARACTERISTICS** ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0 V, I _D =-250μA	-100			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-1	μA
		V _{DS} =-100V, T _C =125°C			-10	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±25V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250μA	-2.0		-4.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-8.5A			0.18	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =-25V, V _{GS} =0V, f=1.0MHz		1450		pF
Output Capacitance	C _{OSS}			440		pF
Reverse Transfer Capacitance	C _{RSS}			160		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{DS} =-80V, V _{GS} =-10V, I _D =-17A I _G =-1mA (Note 1, 2)		42		nC
Gate Source Charge	Q _{GS}			6		nC
Gate Drain Charge	Q _{GD}			16		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =-50V, V _{GS} =-10V, I _D =-17A, R _G =6Ω (Note 1, 2)		10		ns
Turn-ON Rise Time	t _R			22		ns
Turn-OFF Delay Time	t _{D(OFF)}			48		ns
Turn-OFF Fall-Time	t _F			24		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				-17	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				-52	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-17A			-6	V
Body Diode Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _S =17A, dI _F /dt=100A/μs		85		ns
Body Diode Reverse Recovery Charge	Q _{rr}	(Note 1)		0.6		μC

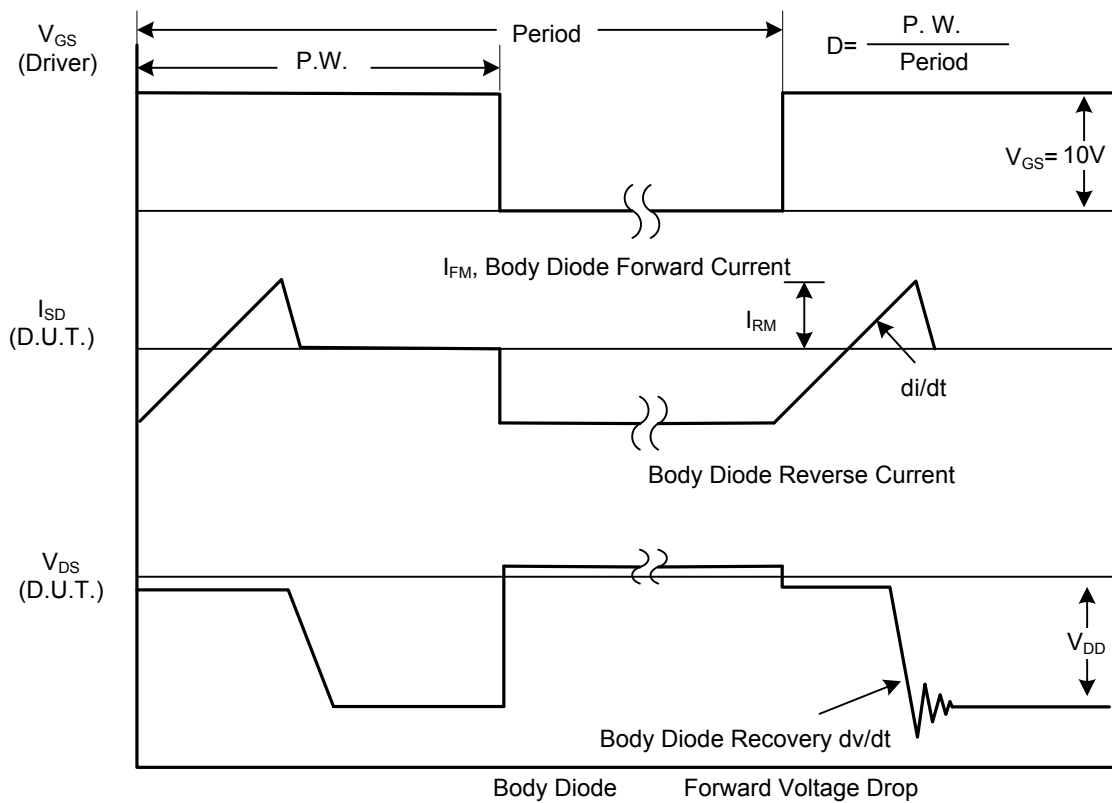
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

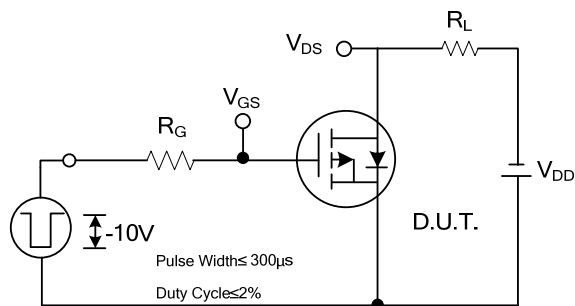


Peak Diode Recovery dv/dt Test Circuit

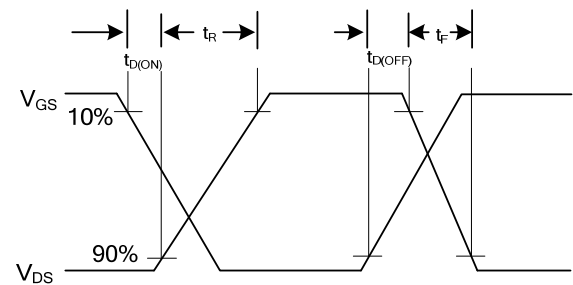


Peak Diode Recovery dv/dt Waveforms

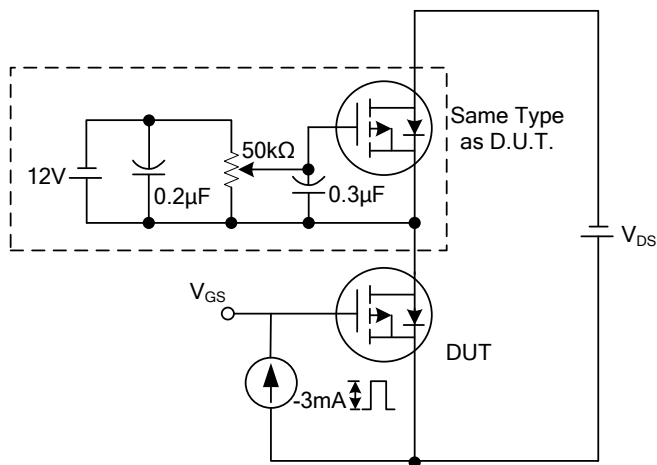
■ TEST CIRCUITS AND WAVEFORMS



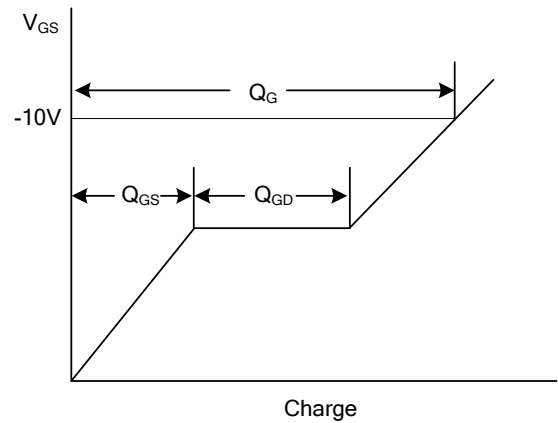
Switching Test Circuit



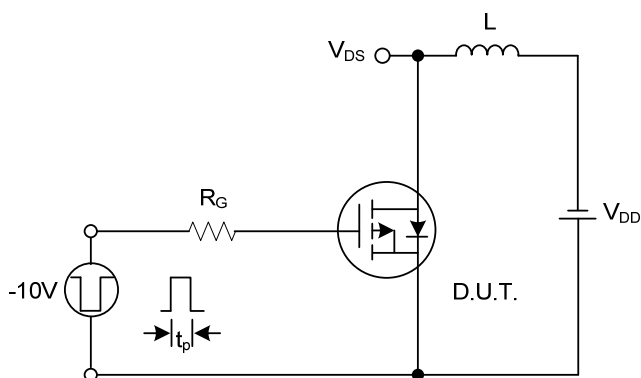
Switching Waveforms



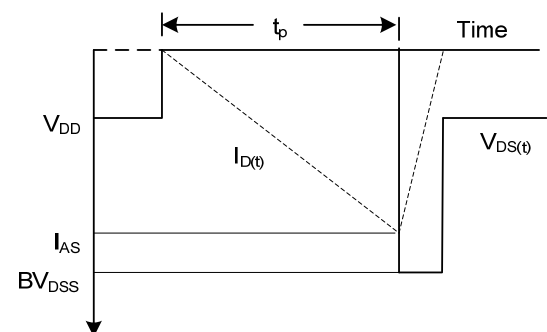
Gate Charge Test Circuit



Gate Charge Waveform

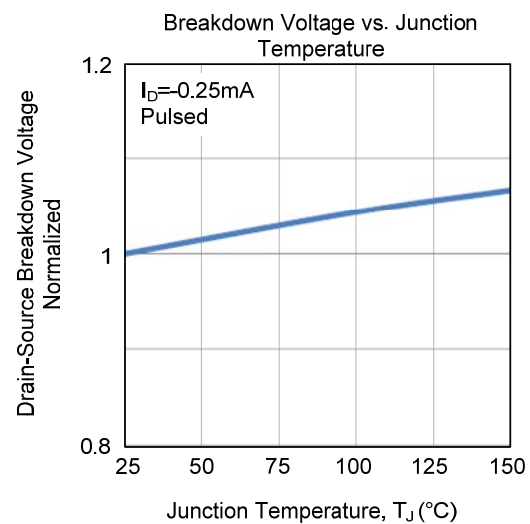
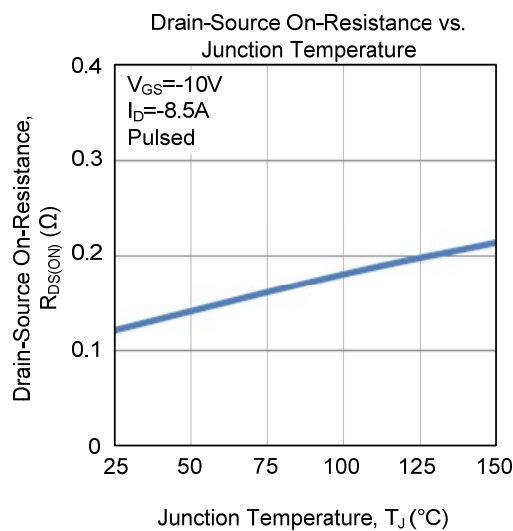
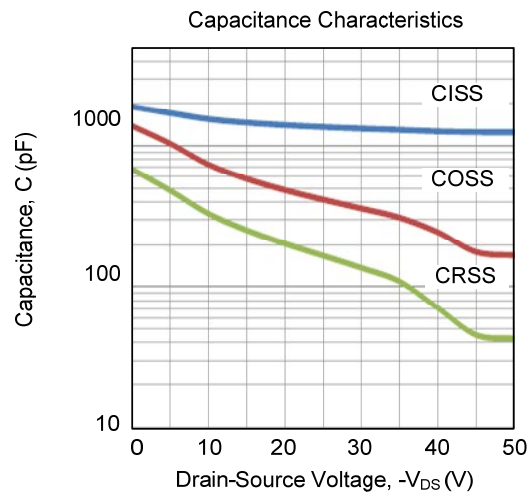
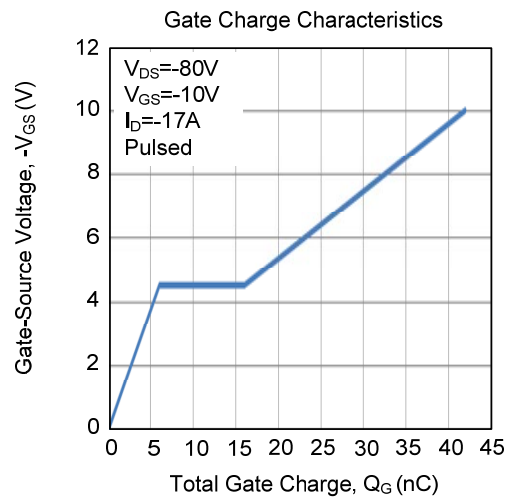
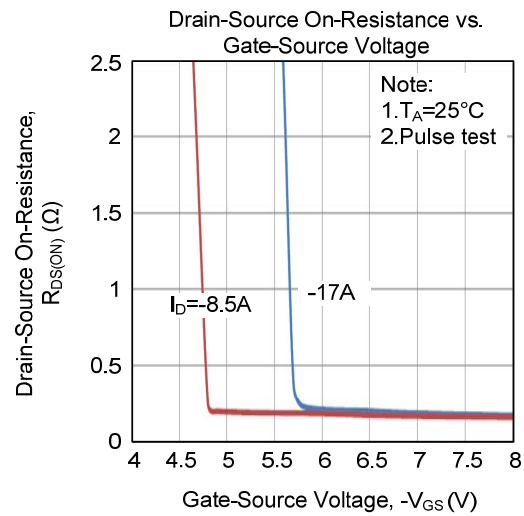
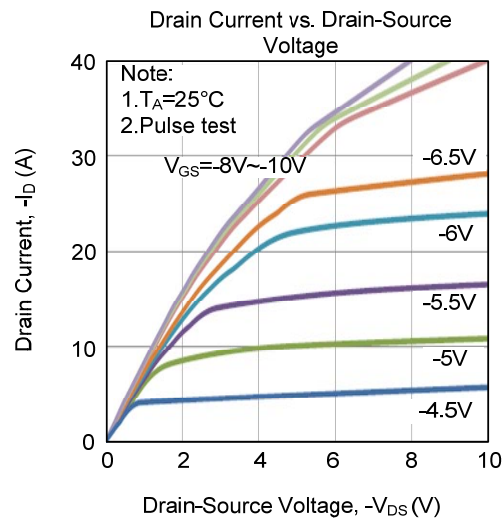


Unclamped Inductive Switching Test Circuit

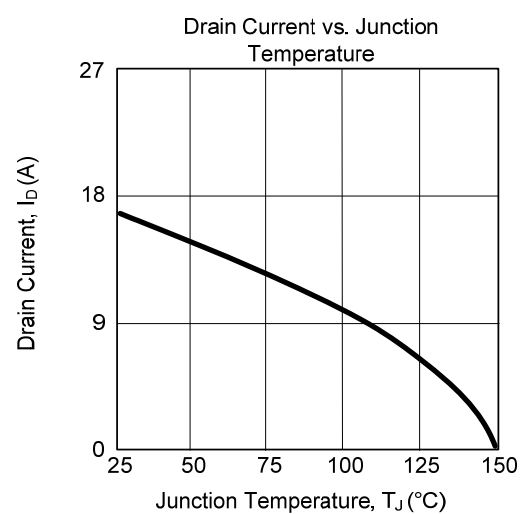
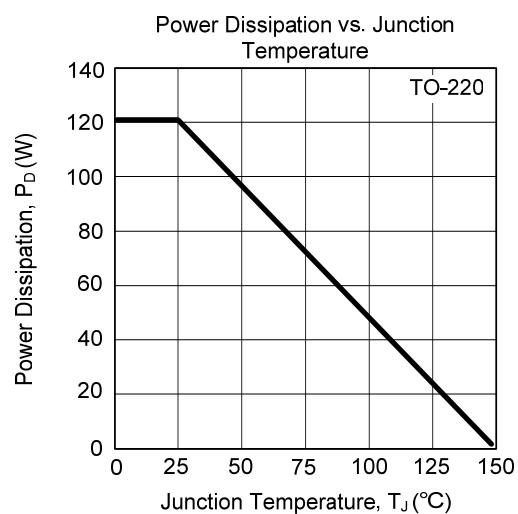
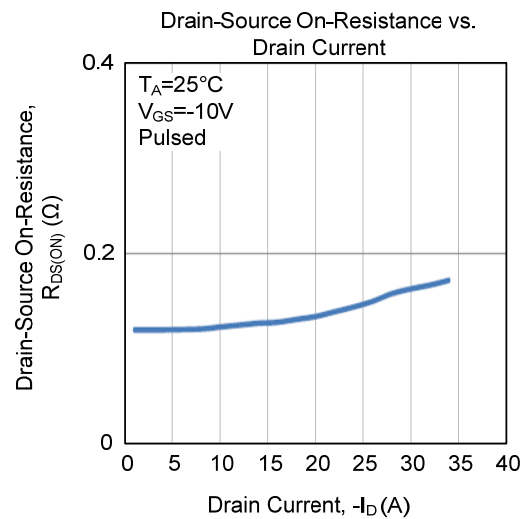
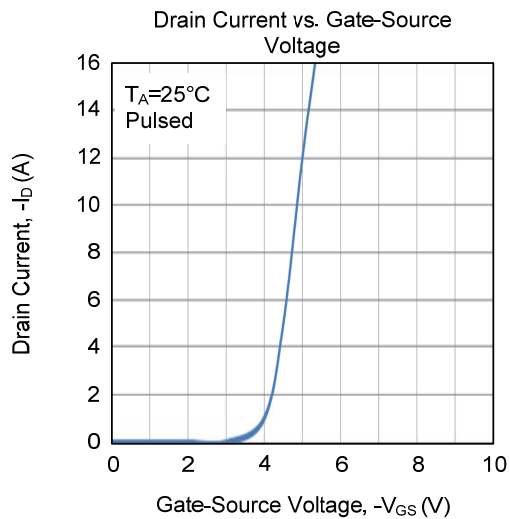
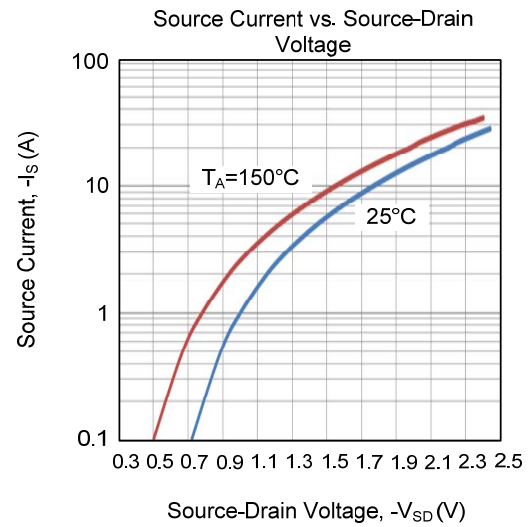
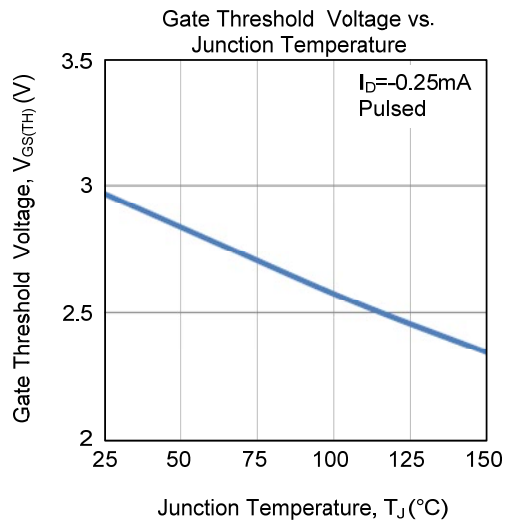


Unclamped Inductive Switching Waveforms

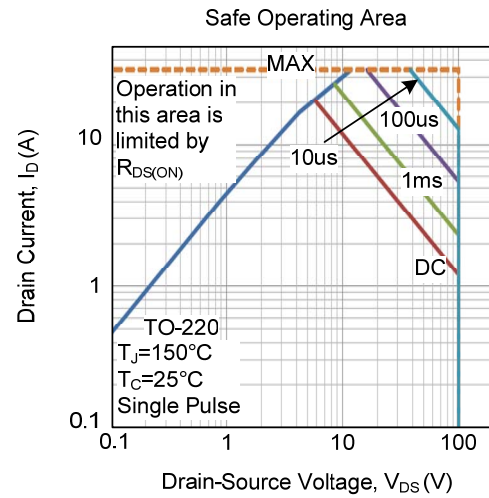
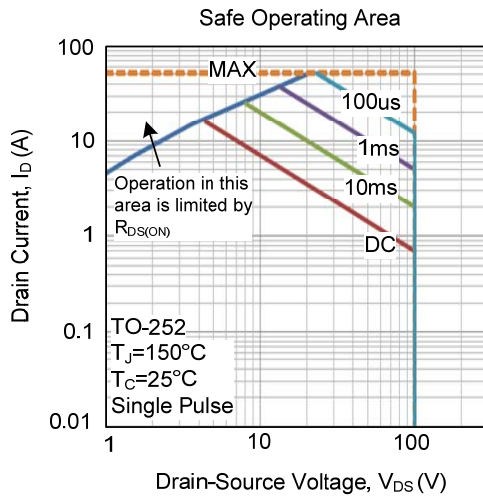
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



TYPICAL CHARACTERISTICS (Cont.)



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